

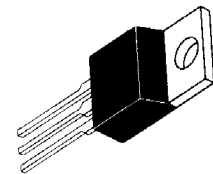
## Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors

... designed for industrial and consumer applications such as temperature, light and speed control; process and remote controls; warning systems; capacitive discharge circuits and MPU interface.

- Center Gate Geometry for Uniform Current Density
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Low Trigger Currents, 200  $\mu$ A Maximum for Direct Driving from Integrated Circuits

### MCR72 Series

SCRs  
8 AMPERES RMS  
50 thru 800 VOLTS



(TO-220AB)

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage <sup>(1)</sup> ( $T_J = -40$ to $110^\circ\text{C}$ , 1/2 Sine Wave, $R_{GK} = 1\text{k}\Omega$ )	$V_{DRM}$ or $V_{RRM}$	50 100 200 400 600 800	Volts
On-State RMS Current ( $T_C = 83^\circ\text{C}$ )	$I_T(\text{RMS})$	8	Amps
Peak Non-repetitive Surge Current (1/2 Cycle, 60 Hz, $T_J = -40$ to $110^\circ\text{C}$ )	$I_{TSM}$	100	Amps
Circuit Fusing ( $t = 8.3$ ms)	$i^2t$	40	$\text{A}^2\text{s}$
Peak Gate Voltage ( $t \leq 10$ $\mu\text{s}$ )	$V_{GM}$	$\pm 5$	Volts
Peak Gate Current ( $t \leq 10$ $\mu\text{s}$ )	$I_{GM}$	1	Amp
Peak Gate Power ( $t \leq 10$ $\mu\text{s}$ )	$P_{GM}$	5	Watts
Average Gate Power	$P_{G(AV)}$	0.75	Watts
Operating Junction Temperature Range	$T_J$	$-40$ to $+110$	$^\circ\text{C}$

1.  $V_{DRM}$  and  $V_{RRM}$  for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



## MCR72 Series

### MAXIMUM RATINGS — continued

Rating	Symbol	Value	Unit
Storage Temperature Range	$T_{stg}$	-40 to + 150	°C
Mounting Torque	—	8	in. lb.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ , $R_{GK} = 1\text{ k}\Omega$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current(1) ( $V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}$ ) $T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$	$I_{DRM}, I_{RRM}$	— —	— —	10 500	$\mu\text{A}$ $\mu\text{A}$
On-State Voltage ( $I_{TM} = 16\text{ A Peak}$ , Pulse Width $\leq 1\text{ ms}$ , Duty Cycle $\leq 2\%$ )	$V_{TM}$	—	1.7	2	Volts
Gate Trigger Current (Continuous dc)(2) ( $V_D = 12\text{ V}$ , $R_L = 100\ \Omega$ )	$I_{GT}$	—	30	200	$\mu\text{A}$
Gate Trigger Voltage (Continuous dc) ( $V_D = 12\text{ V}$ , $R_L = 100\ \Omega$ ) ( $V_D = \text{Rated } V_{DRM}$ , $R_L = 10\text{ k}\Omega$ , $T_J = 110^\circ\text{C}$ )	$V_{GT}$	— 0.1	0.5 —	1.5 —	Volts
Holding Current ( $V_D = 12\text{ V}$ , $I_{TM} = 100\text{ mA}$ )	$I_H$	—	—	6	mA
Critical Rate-of-Rise of Forward Blocking Voltage ( $V_D = \text{Rated } V_{DRM}$ , $T_J = 110^\circ\text{C}$ , Exponential Waveform)	$dv/dt$	—	10	—	$\text{V}/\mu\text{s}$
Gate Controlled Turn-On Time ( $V_D = \text{Rated } V_{DRM}$ , $I_{TM} = 16\text{ A}$ , $I_G = 2\text{ mA}$ )	$t_{gt}$	—	1	—	$\mu\text{s}$

1. Ratings apply for negative gate voltage or  $R_{GK} = 1\text{ k}\Omega$ . Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.
2. Does not include  $R_{GK}$  current.